



ACJT1 Series 1A TRIACs

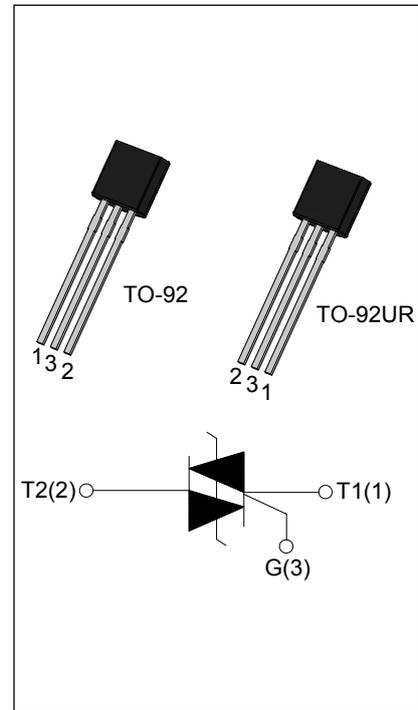
Rev.8.0

DESCRIPTION:

ACJT1 series triacs with high ability to withstand the shock loading of large current provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on inductive load and serious electromagnetic interference place. Package TO-92 & TO-92UR are RoHS compliant. (2011/65/EU)

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	600/800/1000	V
I_{GT}	≤ 5 or ≤ 10	mA



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range		T_j	-40-125	$^{\circ}C$
Repetitive peak off-state voltage($T_j=25^{\circ}C$)		V_{DRM}	600/800/1000	V
Repetitive peak reverse voltage($T_j=25^{\circ}C$)		V_{RRM}	600/800/1000	V
RMS on-state current	TO-92/ TO-92UR ($T_C=50^{\circ}C$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	10	A
I^2t value for fusing ($t_p=10ms$)		I^2t	1.12	A^2s
Rate of rise of on-state current ($I_G=2 \times I_{GT}$)		di_T/dt	50	$A/\mu s$
Peak gate current		I_{GM}	1	A
Average gate power dissipation		$P_{G(AV)}$	0.2	W
Peak gate power		P_{GM}	1	W

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value		Unit
				ACJT105	ACJT110	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	5	10	mA
V_{GT}		I - II -III	MAX	1.3		V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2		V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	15	25	mA
		II		25	35	
I_H	$I_T=100\text{mA}$		MAX	10	20	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN	400	600	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=1.4\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	0.5	mA

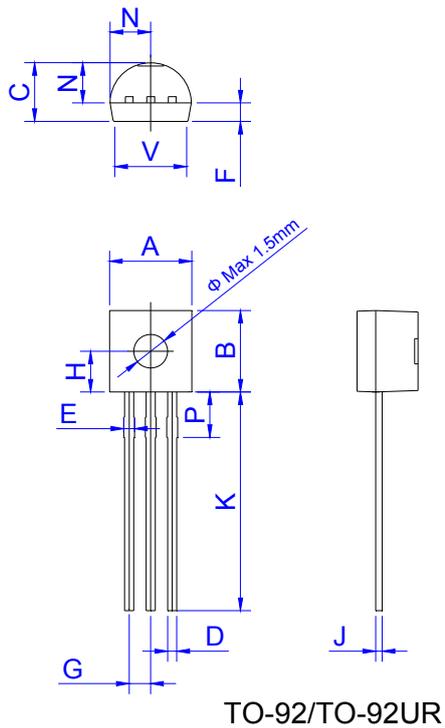
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-92	60	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION

<p>AC AC switch JieJie Microelectronics Co.,Ltd</p>	<p>J Triacs $I_{T(RMS)}:1\text{A}$</p>	<p>T</p>	<p>1</p>	<p>05 05: $I_{GT1-3} \leq 5\text{mA}$ 10: $I_{GT1-3} \leq 10\text{mA}$</p>	<p>-6 6: $V_{DRM} / V_{RRM} \geq 600\text{V}$ 8: $V_{DRM} / V_{RRM} \geq 800\text{V}$ 10: $V_{DRM} / V_{RRM} \geq 1000\text{V}$</p>	<p>U U: TO-92 UR: TO-92UR</p>
--	--	-----------------	-----------------	---	---	--

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.50		0.70	0.024		0.031
F	-	1.1	-	-	0.043	-
G	-	1.27	-	-	0.050	-
H	-	2.30	-	-	0.091	-
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.86		2.06	0.073		0.081
V	-		4.3	-		0.169

PACKAGE INFORMATION

PACKAGE	WEIGHT (PER PCS)	OUTLINE	BAG (PCS)	INNER BOX (PCS)	PER CARTON
TO-92/ TO-92UR	0.1894g	Shielding Bag	1,000	10,000	30,000

FIG.1 Maximum power dissipation versus RMS on-state current

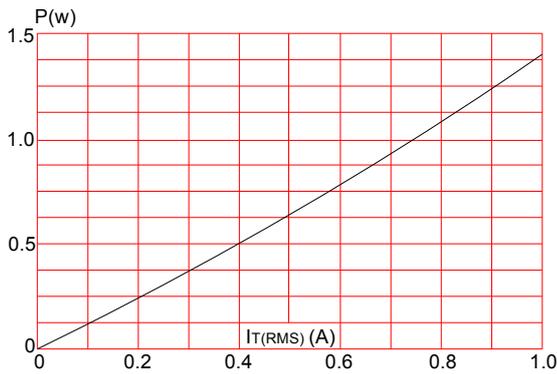


FIG.2: RMS on-state current versus case temperature

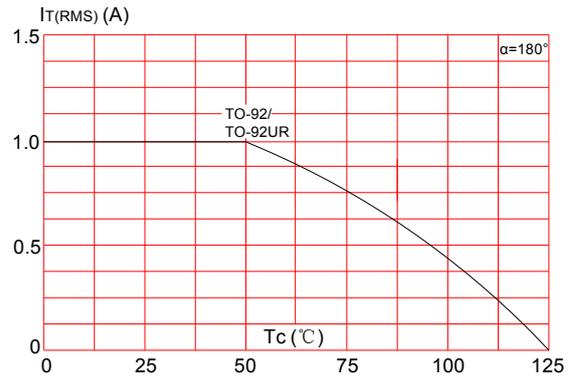


FIG.3: Surge peak on-state current versus number of cycles

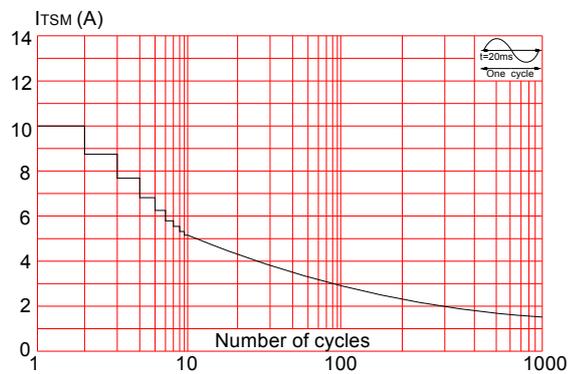


FIG.4: On-state characteristics (maximum values)

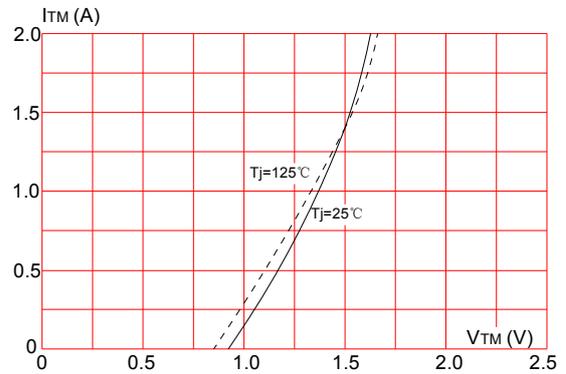


FIG.5: Relative variations of gate trigger current versus junction temperature

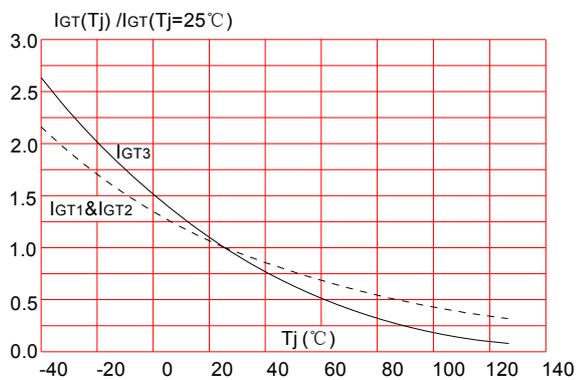
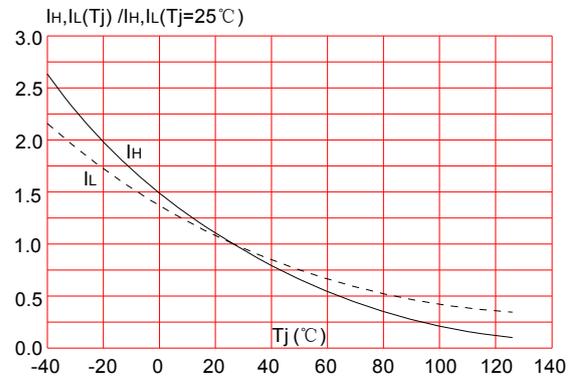


FIG.6: Relative variations of holding current, latching current versus junction temperature



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co.,Ltd assumes no responsibility for the consequences of use without consideration for such information nor use beyond it.

Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information.

This document is the eighth version which is made in 10-June-2019. This document supersedes and replaces all information previously supplied.

 is a registered trademark of Jiangsu JieJie Microelectronics Co.,Ltd.

Copyright ©2019 Jiangsu JieJie Microelectronics Co.,Ltd. Printed All rights reserved.
